onsemi™

High-Power PNP Silicon Transistor

MJ4502

This transistor is for use as an output device in complementary audio amplifiers to 100-Watts music power per channel.

Features

- High DC Current Gain − h_{FE} = 25−100 @ I_C = 7.5 A
- Excellent Safe Operating Area
- Complement to the NPN MJ802
- Pb−Free Package is Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CER}	100	Vdc
Collector-Base Voltage	V_{CB}	100	Vdc
Collector-Emitter Voltage	V_{CEO}	90	Vdc
Emitter-Base Voltage	V_{EB}	4.0	Vdc
Collector Current	I_C	30	Adc
Base Current	I_B	7.5	Adc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	200 1.14	W W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction−to−Case	θ_{JC}	0.875	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

30 AMPERE POWER TRANSISTOR PNP SILICON 100 VOLTS – 200 WATTS
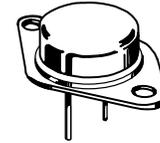
**TO−204AA (TO−3)
CASE 1−07
STYLE 1**

MARKING DIAGRAM

MJ4502G
AYYWW
MEX

MJ4502	= Device Code
G	= Pb−Free Package
A	= Assembly Location
YY	= Year
WW	= Work Week
MEX	= Country of Origin

ORDERING INFORMATION

Device	Package	Shipping[†]
MJ4502G,	TO-204 (Pb-Free)	100 Units / Tray

DISCONTINUED (Note 1)

MJ4502	TO-204	100 Units / Tray

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

1. **DISCONTINUED:** This device is not available. Please contact your **onsemi** representative for information. The most current information on this device may be available on www.onsemi.com.

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_C = 25 °C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector−Emitter Breakdown Voltage (Note 2) (I_C = 200 mAdc, R_{BE} = 100 Ω)	$V_{(BR)CER}$	100	–	Vdc
Collector−Emitter Sustaining Voltage (Note 2) (I_C = 200 mAdc)	$V_{CEO(sus)}$	90	–	Vdc
Collector−Base Cutoff Current (V_{CB} = 100 Vdc, I_E = 0) (V_{CB} = 100 Vdc, I_E = 0, T_C = 150°C)	I_{CBO}	 – –	 1.0 5.0	mAdc
Emitter−Base Cutoff Current (V_{BE} = 4.0 Vdc, I_C = 0)	I_{EBO}	–	1.0	mAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 7.5 Adc, V_{CE} = 2.0 Vdc)	h_{FE}	25	100	–
Base−Emitter "On" Voltage (I_C = 7.5 Adc, V_{CE} = 2.0 Vdc)	$V_{BE(on)}$	–	1.3	Vdc
Collector−Emitter Saturation Voltage (I_C = 7.5 Adc, I_B = 0.75 Adc)	$V_{CE(sat)}$	–	0.8	Vdc
Base−Emitter Saturation Voltage (I_C = 7.5 Adc, I_B = 0.75 Adc)	$V_{BE(sat)}$	–	1.3	Vdc
DYNAMIC CHARACTERISTICS				
Current Gain − Bandwidth Product (I_C = 1.0 Adc, V_{CE} = 10 Vdc, f = 1.0 MHz)	f_T	2.0	–	MHz

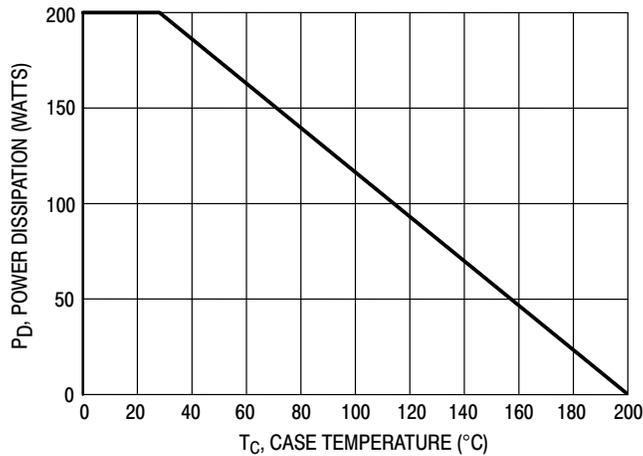2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

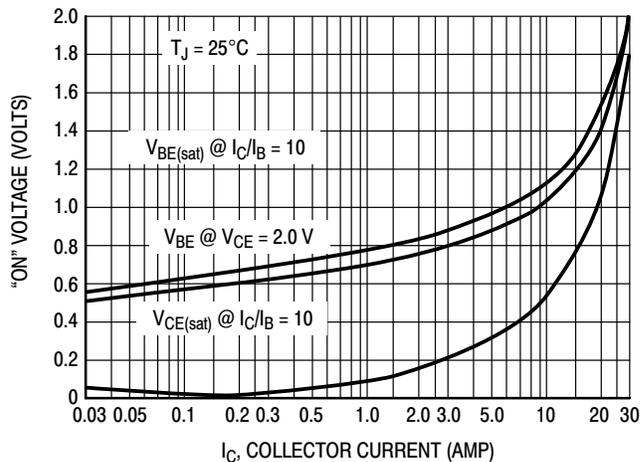**Figure 1. Power−Temperature Derating Curve**
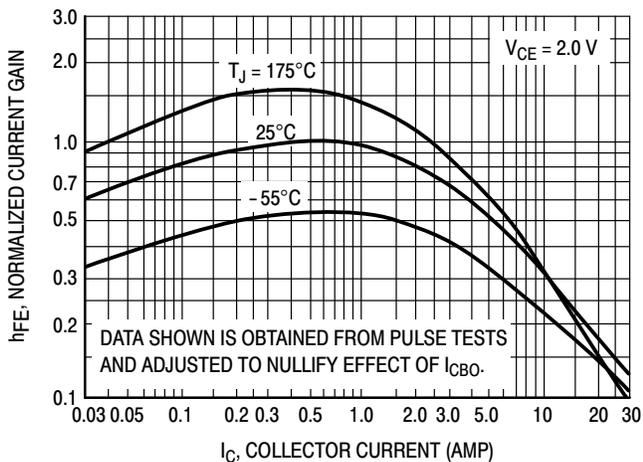
Figure 2. DC Current Gain

Figure 2 axes: hFE, NORMALIZED CURRENT GAIN (vertical, 0.1 to 3.0); IC, COLLECTOR CURRENT (AMP) (horizontal, 0.03 to 30). Curves labeled TJ = 175°C, 25°C, −55°C. VCE = 2.0 V. Note: DATA SHOWN IS OBTAINED FROM PULSE TESTS AND ADJUSTED TO NULLIFY EFFECT OF ICBO.

Figure 3. "On" Voltages

Figure 3 axes: "ON" VOLTAGE (VOLTS) (vertical, 0 to 2.0); IC, COLLECTOR CURRENT (AMP) (horizontal, 0.03 to 30). TJ = 25°C. Curves labeled VBE(sat) @ IC/IB = 10, VBE @ VCE = 2.0 V, VCE(sat) @ IC/IB = 10.

Figure 4. Active Region Safe Operating Area

Figure 4 axes: IC, COLLECTOR CURRENT (AMP) (vertical, 0.1 to 100); VCE, COLLECTOR-EMITTER VOLTAGE (VOLTS) (horizontal, 1.0 to 100). Curves labeled 1.0 ms, 100 μs, 5.0 ms, dc. TJ = 200°C. Legend: SECONDARY BREAKDOWN LIMITED, BONDING WIRE LIMITED, THERMAL LIMITATIONS @ TC = 25°C, PULSE DUTY CYCLE ≤ 10%.

The Safe Operating Area Curves indicate $I_C - V_{CE}$ limits below which the device will not enter secondary breakdown. Collector load lines for specific circuits must fall within the applicable Safe Area to avoid causing a catastrophic failure. To insure operation below the maximum T_J, power−temperature derating must be observed for both steady state and pulse power conditions.

MJ4502

Revision	Description of Changes	Date
13	MJ4502 OPN Marked as Discontinued + Rebranded the Data Sheet to onsemi format	8/27/2025

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.
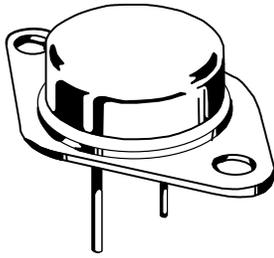
TO–204 (TO–3)
CASE 1–07
ISSUE Z

DATE 10 MAR 2000

SCALE 1:1
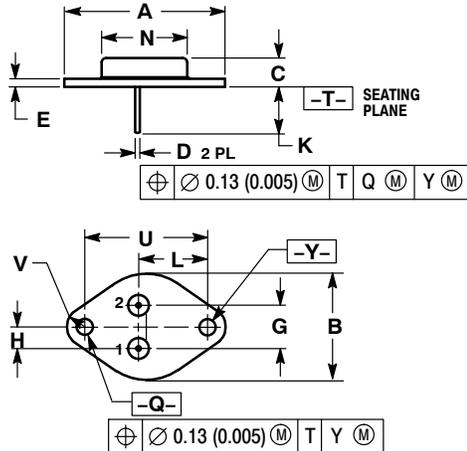
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO–204AA OUTLINE SHALL APPLY.

⊕ ⌀ 0.13 (0.005) Ⓜ T Q Ⓜ Y Ⓜ

⊕ ⌀ 0.13 (0.005) Ⓜ T Y Ⓜ

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.550 REF		39.37 REF	
B	---	1.050	---	26.67
C	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
E	0.055	0.070	1.40	1.77
G	0.430 BSC		10.92 BSC	
H	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N	---	0.830	---	21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15 BSC	
V	0.131	0.188	3.33	4.77

STYLE 1:
PIN 1. BASE
2. EMITTER
CASE: COLLECTOR

STYLE 2:
PIN 1. BASE
2. COLLECTOR
CASE: EMITTER

STYLE 3:
PIN 1. GATE
2. SOURCE
CASE: DRAIN

STYLE 4:
PIN 1. GROUND
2. INPUT
CASE: OUTPUT

STYLE 5:
PIN 1. CATHODE
2. EXTERNAL TRIP/DELAY
CASE: ANODE

STYLE 6:
PIN 1. GATE
2. EMITTER
CASE: COLLECTOR

STYLE 7:
PIN 1. ANODE
2. OPEN
CASE: CATHODE

STYLE 8:
PIN 1. CATHODE #1
2. CATHODE #2
CASE: ANODE

STYLE 9:
PIN 1. ANODE #1
2. ANODE #2
CASE: CATHODE

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DESCRIPTION:	TO–204 (TO–3)		PAGE 1 OF 1

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